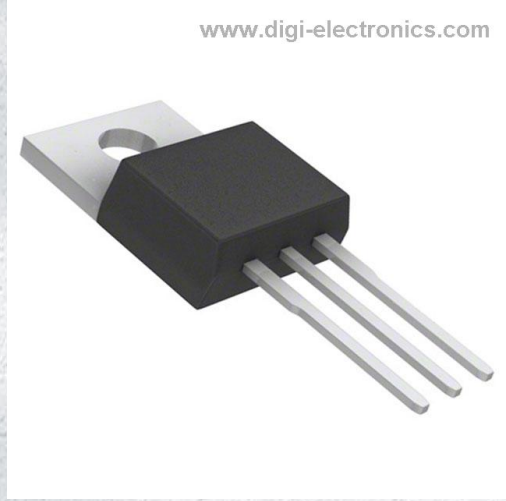
FJP5027TU Datasheet



DiGi Electronics Part Number	FJP5027TU-DG
Manufacturer	onsemi
Manufacturer Product Number	FJP5027TU
Description	TRANS NPN 800V 3A TO220-3
Detailed Description	Bipolar (BJT) Transistor NPN 800 V 3 A 15MHz 50 W Through Hole TO-220-3

https://www.DiGi-Electronics.com

Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

Purchase and inquiry

Manufacturer Product Number:	Manufacturer:
FJP5027TU	onsemi
Series:	Product Status:
-	Obsolete
Transistor Type:	Current - Collector (Ic) (Max):
NPN	3 A
Voltage - Collector Emitter Breakdown (Max):	Vce Saturation (Max) @ Ib, Ic:
800 V	2V @ 300mA, 1.5A
Current - Collector Cutoff (Max):	DC Current Gain (hFE) (Min) @ Ic, Vce:
10µA (ICBO)	10 @ 200mA, 5V
Power - Max:	Frequency - Transition:
50 W	15MHz
Operating Temperature:	Mounting Type:
150°C (TJ)	Through Hole
Package / Case:	Supplier Device Package:
TO-220-3	TO-220-3
Base Product Number:	
FJP5027	

Environmental & Export classification

Moisture Sensitivity Level (MSL):	REACH Status:
1 (Unlimited)	REACH Unaffected
ECCN:	HTSUS:
EAR99	8541.29.0095

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ON Semiconductor®

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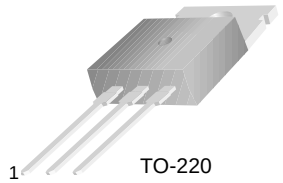
www.onsemi.com

Please note: As part of the Fairchild Semiconductor integration, some of the Fairchild orderable part numbers will need to change in order to meet ON Semiconductor's system requirements. Since the ON Semiconductor product management systems do not have the ability to manage part nomenclature that utilizes an underscore (_), the underscore (_) in the Fairchild part numbers will be changed to a dash (-). This document may contain device numbers with an underscore (_). Please check the ON Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at www.onsemi.com. Please email any questions regarding the system integration to Fairchild_questions@onsemi.com.

FJP5027

High Voltage and High Reliability

- High Speed Switching
- Wide SOA



TO-220

1.Base 2.Collector 3.Emitter

NPN Silicon Transistor

Absolute Maximum Ratings T_C=25°C unless otherwise noted

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	1100	V
V_{CEO}	Collector-Emitter Voltage	800	V
V_{EBO}	Emitter-Base Voltage	7	V
I_C	Collector Current (DC)	3	A
I_{CP}	Collector Current (Pulse)	10	A
I_B	Base Current	1.5	A
P_C	Collector Dissipation (T_C=25°C)	50	W
T_J	Junction Temperature	150	°C
T_{STG}	Storage Temperature	- 55 ~ 150	°C

Electrical Characteristics T_C=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
BV_{CBO}	Collector-Base Breakdown Voltage	I_C = 1mA, I_E = 0	1100			V
BV_{CEO}	Collector-Emitter Breakdown Voltage	I_C = 5mA, I_B = 0	800			V
BV_{EBO}	Emitter-Base Breakdown Voltage	I_E = 1mA, I_C = 0	7			V
V_{CEX}(sus)	Collector-Emitter Sustaining Voltage	I_C = 1.5A, I_{B1} = -I_{B2} = 0.3A L = 2mH, Clamped	800			V
I_{CBO}	Collector Cut-off Current	V_{CB} = 800V, I_E = 0			10	µA
I_{EBO}	Emitter Cut-off Current	V_{EB} = 5V, I_C = 0			10	µA
h_{FE1} h_{FE2}	DC Current Gain	V_{CE} = 5V, I_C = 0.2A V_{CE} = 5V, I_C = 1A	10 8		40	
V_{CE}(sat)	Collector-Emitter Saturation Voltage	I_C = 1.5A, I_B = 0.3A			2	V
V_{BE}(sat)	Base-Emitter Saturation Voltage	I_C = 1.5A, I_B = 0.3A			1.5	V
C_{ob}	Output Capacitance	V_{CB} = 10V, I_E = 0, f = 1MHz		60		pF
f_T	Current Gain Bandwidth Product	V_{CE} = 10V, I_C = 0.2A		15		MHz
t_{ON}	Turn On Time	V_{CC} = 400V I_C = 5I_{B1} = -2.5I_{B2} = 2A R_L = 200Ω			0.5	µs
t_{STG}	Storage Time				3	µs
t_F	Fall Time				0.3	µs

h_{FE} Classification

Classification	N	R	O
h_{FE1}	10 ~ 20	15 ~ 30	20 ~ 40

Typical Characteristics

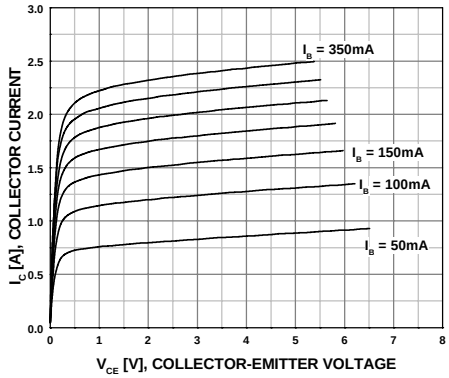


Figure 1. Static Characteristic

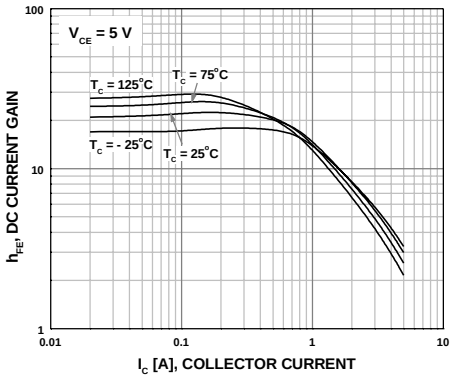


Figure 2. DC current Gain

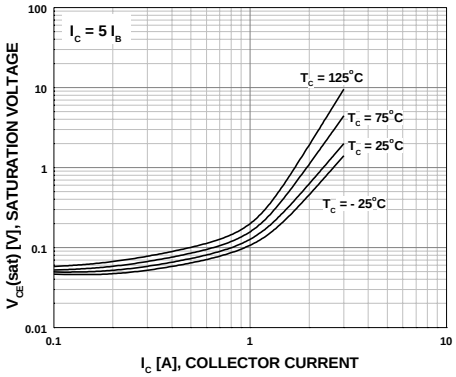


Figure 3. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

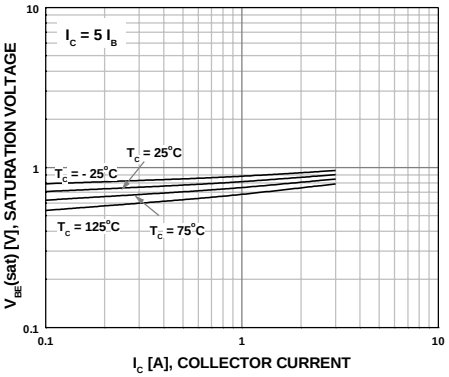


Figure 4. Base-Emitter On Voltage

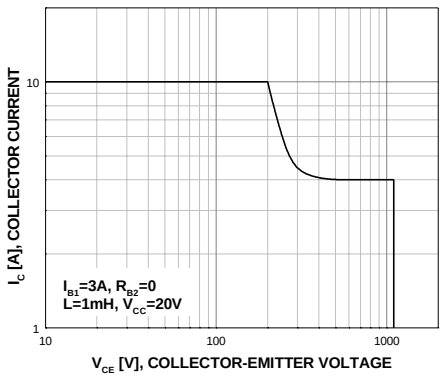


Figure 5. Switching Time

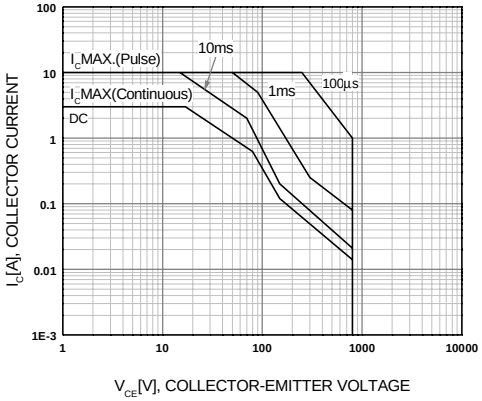


Figure 6. Safe Operating Area

Typical Characteristics (Continued)

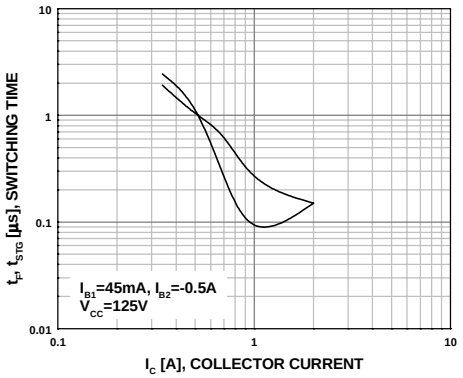


Figure 7. Resistive Load Switching Characteristics

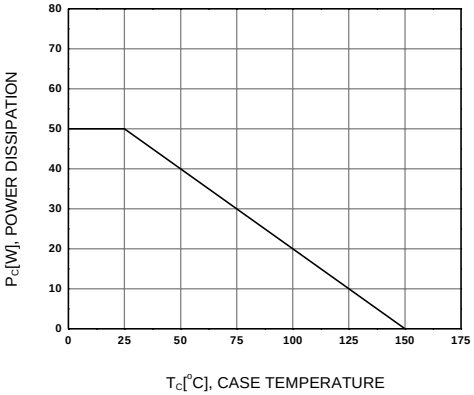
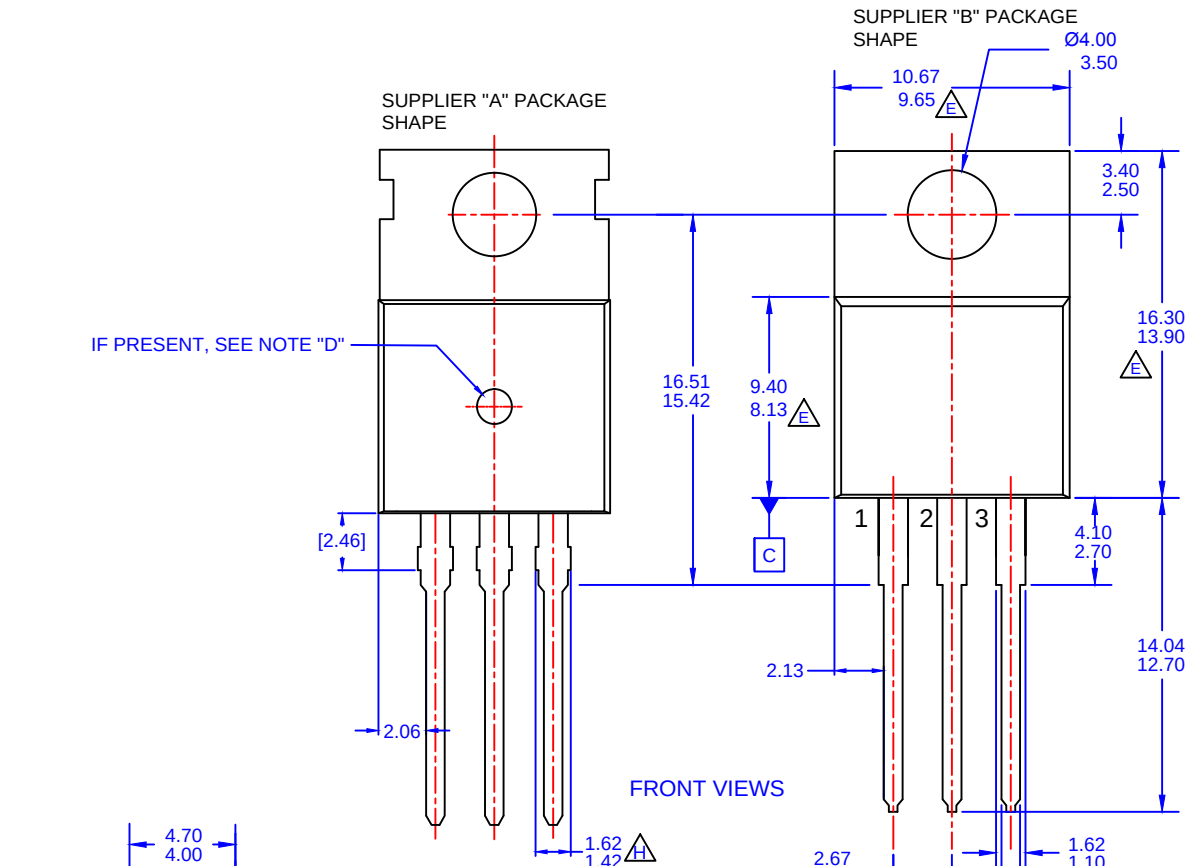
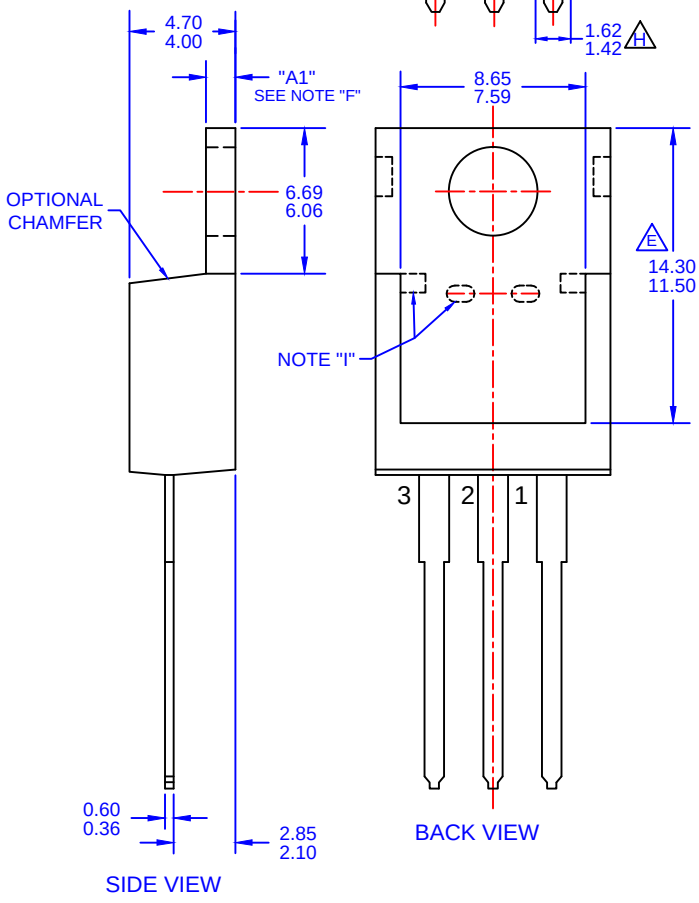


Figure 8. Power Derating





NOTES:

A) REFERENCE JEDEC, TO-220, VARIATION AB
B) ALL DIMENSIONS ARE IN MILLIMETERS.
C) DIMENSIONS COMMON TO ALL PACKAGE SUPPLIERS EXCEPT WHERE NOTED [ ].
D) LOCATION OF MOLDED FEATURE MAY VARY (LOWER LEFT CORNER, LOWER CENTER AND CENTER OF THE PACKAGE)
E DOES NOT COMPLY JEDEC STANDARD VALUE.
F) "A1" DIMENSIONS AS BELOW:
SINGLE GAUGE = 0.51 - 0.61
DUAL GAUGE = 1.10 - 1.45
G) DRAWING FILE NAME: TO220B03REV9
H PRESENCE IS SUPPLIER DEPENDENT
I) SUPPLIER DEPENDENT MOLD LOCKING HOLES IN HEATSINK.

FAIRCHILD

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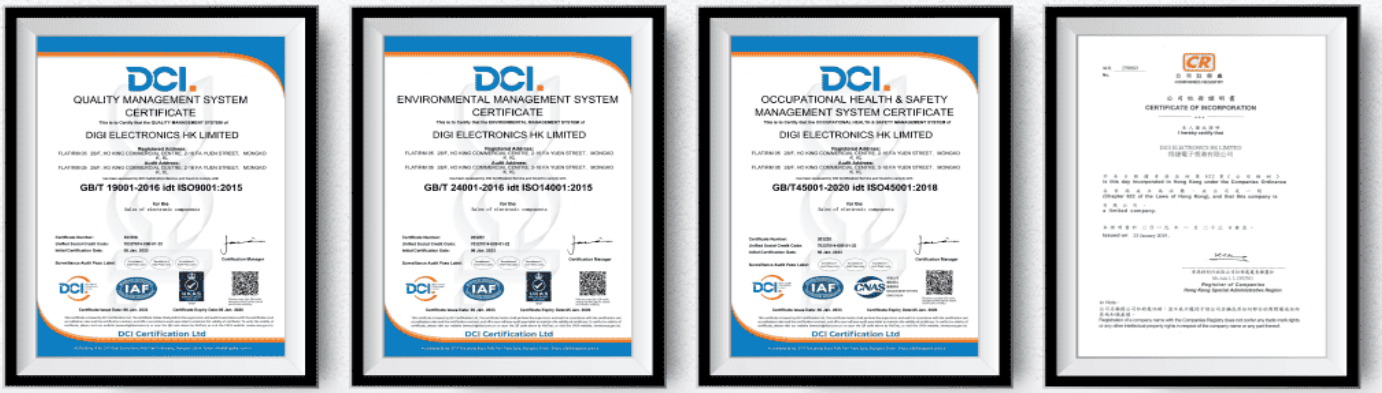

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